

# TXS0104V 4-Bit Bi-directional, Level-Shifting, Voltage Translator for Open-Drain and Push-Pull Applications

## 1 Features

- No direction-control signal needed
- Maximum data rates:
  - 24Mbps (push pull)
  - 2Mbps (open drain)
- 1.65V to 3.6V on A port and 2.3V to 5.5V on B port ( $V_{CCA} \leq V_{CCB}$ )
- No power-supply sequencing required –  $V_{CCA}$  or  $V_{CCB}$  can be ramped first
- Latch-up performance exceeds 100mA per JESD 78, class II
- ESD protection exceeds JESD 22:
  - A port:
    - 2000V Human-Body Model (A114-B)
    - 500V Charged-Device Model (C101)
  - B port:
    - 5000V Human-Body Model (A114-B)
    - 500V Charged-Device Model (C101)

## 2 Applications

- [Handset](#)
- [Smartphone](#)
- [Tablet](#)
- [Desktop PC](#)

## 3 Description

This 4-bit non-inverting translator uses two separate configurable power-supply rails. The A port is designed to track  $V_{CCA}$ .  $V_{CCA}$  accepts any supply voltage from 1.65V to 3.6V.  $V_{CCA}$  must be less than or equal to  $V_{CCB}$ . The B port is designed to track  $V_{CCB}$ .  $V_{CCB}$  accepts any supply voltage from 2.3V to 5.5V. This allows for low-voltage bidirectional translation between any of the 1.8V, 2.5V, 3.3V, and 5V voltage nodes.

When the output-enable (OE) input is low, all outputs are placed in the high-impedance state.

The TXS0104V is designed so that the OE input circuit is supplied by  $V_{CCA}$ .

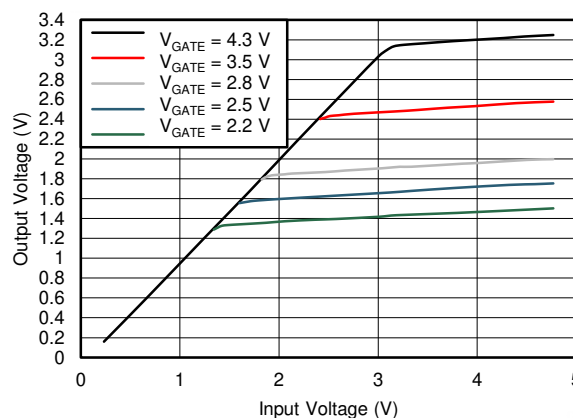
For the high-impedance state during power up or power down, tie OE to GND through a pull-down resistor; the current-sourcing capability of the driver determines the minimum value of the resistor.

### Package Information

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
TXS0104V	PW (TSSOP, 14)	5mm × 6.4mm
	BQA (WQFN, 12)	3mm × 2.5mm
	RUT (UQFN, 12)	2mm × 1.7mm
	RGY (VQFN, 14)	3.5mm × 3.5mm
	D (SOIC, 14)	8.65mm × 6mm

(1) For more information, see [Section 11](#).

(2) The package size (length × width) is a nominal value and includes pins, where applicable.



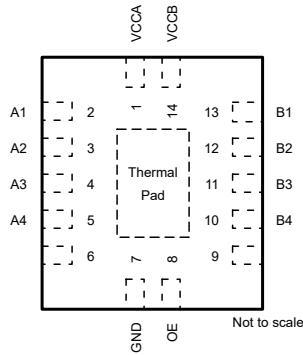
Transfer Characteristics of an N-Channel Transistor



## Table of Contents

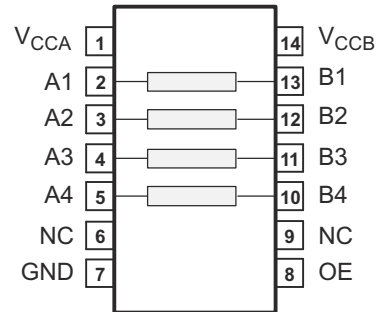
<b>1 Features</b> .....	1	7.1 Overview.....	13
<b>2 Applications</b> .....	1	7.2 Functional Block Diagram.....	13
<b>3 Description</b> .....	1	7.3 Feature Description.....	14
<b>4 Pin Configuration and Functions</b> .....	3	7.4 Device Functional Modes.....	14
<b>5 Specifications</b> .....	5	<b>8 Application and Implementation</b> .....	15
5.1 Absolute Maximum Ratings.....	5	8.1 Application Information.....	15
5.2 ESD Ratings.....	5	8.2 Typical Application.....	15
5.3 Recommended Operating Conditions.....	5	8.3 Power Supply Recommendations.....	17
5.4 Thermal Information (PW, RGY, BQA, RUT, D).....	6	8.4 Layout.....	17
5.5 Electrical Characteristics.....	6	<b>9 Device and Documentation Support</b> .....	18
5.6 Switching Characteristics, $V_{CCA} = 1.8 \pm 0.15V$ .....	7	9.1 Documentation Support.....	18
5.7 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2V$ .....	7	9.2 Receiving Notification of Documentation Updates... 18	
5.8 Switching Characteristics, $V_{CCA} = 3.3 \pm 0.3V$ .....	8	9.3 Support Resources.....	18
5.9 Switching Characteristics: $T_{sk}$ , $T_{MAX}$ .....	9	9.4 Trademarks.....	18
5.10 Typical Characteristics.....	9	9.5 Electrostatic Discharge Caution.....	18
<b>6 Parameter Measurement Information</b> .....	11	9.6 Glossary.....	18
6.1 Load Circuits.....	11	<b>10 Revision History</b> .....	18
6.2 Voltage Waveforms.....	12	<b>11 Mechanical, Packaging, and Orderable Information</b> .....	18
<b>7 Detailed Description</b> .....	13		

## 4 Pin Configuration and Functions



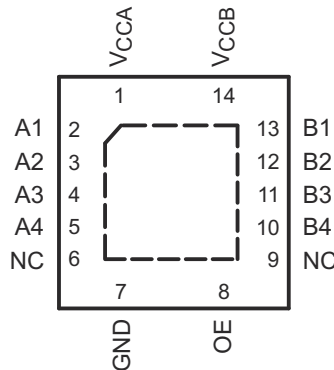
NC - No internal connection

**Figure 4-1. BQA Package, 14-Pin WQFN (Top View)**



NC - No internal connection

**Figure 4-2. D and PW Package, 14-Pin SOIC and TSSOP (Top View)**



NC - No internal connection

**Figure 4-3. RGY Package, 14-Pin VQFN (Top View)**

**Table 4-1. Pin Functions: BQA, PW, D, or RGY**

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
A1	2	I/O	Input/output A1. Referenced to $V_{CCA}$ .
A2	3	I/O	Input/output A2. Referenced to $V_{CCA}$ .
A3	4	I/O	Input/output A3. Referenced to $V_{CCA}$ .
A4	5	I/O	Input/output A4. Referenced to $V_{CCA}$ .
B1	13	I/O	Input/output B1. Referenced to $V_{CCB}$ .
B2	12	I/O	Input/output B2. Referenced to $V_{CCB}$ .
B3	11	I/O	Input/output B3. Referenced to $V_{CCB}$ .
B4	10	I/O	Input/output B4. Referenced to $V_{CCB}$ .
GND	7	—	Ground
OE	8	I	3-state output-mode enable. Pull OE low to place all outputs in 3-state mode. Referenced to $V_{CCA}$ .
$V_{CCA}$	1	—	A-port supply voltage. $1.65V \leq V_{CCA} \leq 3.6V$ and $V_{CCA} \leq V_{CCB}$ .
$V_{CCB}$	14	—	B-port supply voltage. $2.3V \leq V_{CCB} \leq 5.5V$ .
Thermal Pad		—	For the RGY package, the exposed center thermal pad must be connected to ground

(1) I = input, O = output

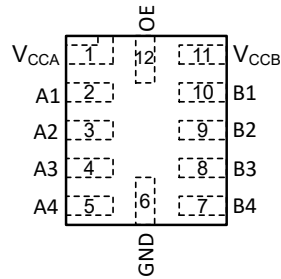


Figure 4-4. RUT Package, 12-Pin UQFN (Transparent Top View)

Table 4-2. Pin Functions: RUT

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
A1	2	I/O	Input/output A1. Referenced to $V_{CCA}$ .
A2	3	I/O	Input/output A2. Referenced to $V_{CCA}$ .
A3	4	I/O	Input/output A3. Referenced to $V_{CCA}$ .
A4	5	I/O	Input/output A4. Referenced to $V_{CCA}$ .
B1	10	I/O	Input/output B1. Referenced to $V_{CCB}$ .
B2	9	I/O	Input/output B2. Referenced to $V_{CCB}$ .
B3	8	I/O	Input/output B3. Referenced to $V_{CCB}$ .
B4	7	I/O	Input/output B4. Referenced to $V_{CCB}$ .
GND	6	—	Ground
OE	12	I	3-state output-mode enable. Pull OE low to place all outputs in 3-state mode. Referenced to $V_{CCA}$ .
$V_{CCA}$	1	—	A-port supply voltage. $1.65V \leq V_{CCA} \leq 3.6V$ and $V_{CCA} \leq V_{CCB}$ .
$V_{CCB}$	11	—	B-port supply voltage. $2.3V \leq V_{CCB} \leq 5.5V$ .

(1) I = input, O = output

## 5 Specifications

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT		
V <sub>CCA</sub>	Supply voltage A		-0.5	4.6	V		
V <sub>CCB</sub>	Supply voltage B		-0.5	6.5	V		
V <sub>I</sub>	Input Voltage <sup>(2)</sup>	I/O Ports (A Port)	-0.5	4.6	V		
		I/O Ports (B Port)	-0.5	6.5			
		OE	-0.5	4.6			
V <sub>O</sub>	Voltage applied to any output in the high-impedance or power-off state <sup>(2)</sup>	A Port	-0.5	4.6	V		
		B Port	-0.5	6.5			
V <sub>O</sub>	Voltage applied to any output in the high or low state <sup>(2) (3)</sup>	A Port	-0.5	V <sub>CCA</sub> + 0.5	V		
		B Port	-0.5	V <sub>CCB</sub> + 0.5			
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-50	mA		
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0		-50	mA		
I <sub>O</sub>	Continuous output current			-50	50	mA	
	Continuous current through V <sub>CC</sub> or GND			-100	100	mA	
T <sub>J</sub>	Junction Temperature				150	°C	
T <sub>stg</sub>	Storage temperature				-65	150	°C

- (1) Operation outside the *Absolute Maximum Rating* may cause permanent device damage. *Absolute Maximum Rating* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Condition*. If used outside the *Recommended Operating Condition* but within the *Absolute Maximum Rating*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The output positive-voltage rating may be exceeded up to 6.5V maximum if the output current rating is observed.

### 5.2 ESD Ratings

			VALUE	UNIT	
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	A Port	±2000	V
			B Port	±5000	
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	A Port	±500	
			B Port	±500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) <sup>(1) (2) (3)</sup>

		V <sub>CCA</sub>	V <sub>CCB</sub>	MIN	MAX	UNIT		
V <sub>CCA</sub>	Supply voltage A			1.65	3.6	V		
V <sub>CCB</sub>	Supply voltage B			2.3	5.5	V		
V <sub>IH</sub>	High-level input voltage	A-port I/O's	1.65V to 1.95V	2.3V to 5.5V	V <sub>CCI</sub> - 0.2	V <sub>CCI</sub>	V	
			2.3V to 3.6V	2.3V to 5.5V	V <sub>CCI</sub> - 0.4	V <sub>CCI</sub>		
		B-port I/O's	1.65V to 3.6V	2.3V to 5.5V	V <sub>CCI</sub> - 0.4	V <sub>CCI</sub>		
		OE Input	1.65V to 3.6V	2.3V to 5.5V	V <sub>CCA</sub> × 0.65	5.5		
V <sub>IL</sub>	Low-level input voltage	A-port I/O's	1.65V to 3.6V	2.3V to 5.5V		0.2	V	
		B-port I/O's	1.65V to 3.6V	2.3V to 5.5V		0.2		
		OE Input	1.65V to 3.6V	2.3V to 5.5V		V <sub>CCA</sub> × 0.35		
Δt/Δv	Input transition rise and fall time	Push-Pull Driving	1.65V to 3.6V	2.3V to 5.5V		10	ns/V	
T <sub>A</sub>	Operating free-air temperature					-40	85	°C

- (1) V<sub>CCI</sub> is the V<sub>CC</sub> associated with the input port.
- (2) V<sub>CCO</sub> is the V<sub>CC</sub> associated with the output port.

- (3) All control inputs and data I/Os of this device have weak pulldowns to ensure the line is not floating when undefined external to the device. The input leakage from these weak pulldowns is defined by the  $I_I$  specification indicated under [Electrical Characteristics](#).

### 5.4 Thermal Information (PW, RGY, BQA, RUT, D)

THERMAL METRIC <sup>(1)</sup>		TXS0104V					UNIT
		PW (TSSOP)	RGY (VQFN)	BQA (WQFN)	RUT (UQFN)	D (SOIC)	
		14 PINS	14 PINS	14 PINS	12 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	115.2	52.9	73.5	150.4	93.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	46.2	54.3	76.9	68.6	53.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	70.9	28.4	43.0	76.3	52.0	°C/W
$Y_{JT}$	Junction-to-top characterization parameter	3.4	2.7	4.7	2.4	13.4	°C/W
$Y_{JB}$	Junction-to-board characterization parameter	70.2	28.3	42.9	76.2	51.6	°C/W
$R_{\theta JC(bottom)}$	Junction-to-case (bottom) thermal resistance	N/A	12.0	19.6	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

### 5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)<sup>(1) (2)</sup>

PARAMETER		TEST CONDITIONS	$V_{CCA}$	$V_{CCB}$	Operating free-air temperature ( $T_A$ )						UNIT
					25°C			-40°C to 85°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
$V_{OHA}$	Port A output high voltage <sup>(3)</sup>	$I_{OH} = -20\mu A$	1.65V to 3.6V	2.3V to 5.5V	$V_{CCA} \times 0.8$			$V_{CCA} \times 0.8$			V
$V_{OLA}$	Low-level output voltage <sup>(4)</sup>	$I_{OL} = 1mA$	1.65V to 3.6V	2.3V to 5.5V	0.4			0.4			V
$V_{OHB}$	Port B output high voltage	$I_{OH} = -20\mu A$	1.65V to 3.6V	2.3V to 5.5V	$V_{CCB} \times 0.8$			$V_{CCB} \times 0.8$			V
$V_{OLB}$	Low-level output voltage <sup>(4)</sup>	$I_{OL} = 1mA$	1.65V to 3.6V	2.3V to 5.5V	0.4			0.4			V
$I_I$	Input leakage current	OE $V_I = V_{CC}$ or GND	1.65V to 3.6V	2.3V to 5.5V	-2			2			$\mu A$
$I_{OZ}$	Tri-state output current	A or B Port: $V_I = V_{CC1}$ or GND $V_O = V_{CC0}$ or GND OE = GND	1.65V to 3.6V	2.3V to 5.5V	-1			1			$\mu A$
$I_{CCA}$	$V_{CCA}$ supply current	$V_I = V_{CC1}$ or GND $I_O = 0$	1.65V to $V_{CCB}$	2.3V to 5.5V	2.4			3.3			$\mu A$
			0V	5.5V	-3			-3			
			3.6V	0V	2.2			2.2			
$I_{CCB}$	$V_{CCB}$ supply current	$V_I = V_{CC1}$ or GND $I_O = 0$	1.65V to $V_{CCB}$	2.3V to 5.5V	12			12			$\mu A$
			0V	5.5V	5			5			
			3.6V	0V	-1			-1			
$I_{CCA} + I_{CCB}$	Combined supply current	$V_I = V_{CC1}$ or GND $I_O = 0$	1.65V to $V_{CCB}$	2.3V to 5.5V	15			15			$\mu A$
$C_i$	Control Input Capacitance	$V_I = 3.3V$ or GND	3.3V	3.3V	6			6			pF
$C_{io}$	Data I/O Capacitance	A or B Port	3.3V	3.3V	5 6.5		12 16.5		pF		

- (1)  $V_{CC1}$  is the  $V_{CC}$  associated with the input port  
 (2)  $V_{CC0}$  is the  $V_{CC}$  associated with the output port  
 (3) Tested at  $V_I = V_{T+(MAX)}$

(4) Tested at  $V_I = V_{T-(MIN)}$

### 5.6 Switching Characteristics, $V_{CCA} = 1.8 \pm 0.15V$

over operating free-air temperature range (unless otherwise noted)

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage ( $V_{CCB}$ )						UNIT			
					2.5 ± 0.2V			3.3 ± 0.3V				5.0 ± 0.5V		
					MIN	TYP	MAX	MIN	TYP	MAX		MIN	TYP	MAX
$t_{PHL}$	Propagation Delay (High-to-Low)	A	B	Push-Pull	4			4			5			ns
$t_{PHL}$	Propagation Delay (High-to-Low)			Open-Drain	8.8			9.6			10			ns
$t_{PLH}$	Propagation Delay (Low-to-High)			Push-Pull	6			6			6			ns
$t_{PLH}$	Propagation Delay (Low-to-High)			Open-Drain	200			160			120			ns
$t_{PHL}$	Propagation Delay (High-to-Low)	B	A	Push-Pull	4			4			4			ns
$t_{PHL}$	Propagation Delay (High-to-Low)			Open-Drain	5.3			4.4			4.1			ns
$t_{PLH}$	Propagation Delay (Low-to-High)			Push-Pull	5			4			4			ns
$t_{PLH}$	Propagation Delay (Low-to-High)			Open-Drain	173			120			90			ns
$t_{en}$	Enable Time	OE	A or B	-40°C to 85°C	200			200			200			ns
$t_{dis}$	Disable Time	OE	A or B	-40°C to 85°C	250			250			250			ns
$t_{rA}$	Output Rise Time	B	A	Push-Pull	9			9			7			ns
$t_{rA}$	Output Rise Time			Open-Drain	150			120			80			ns
$t_{rB}$	Output Rise Time	A	B	Push-Pull	10			9			7			ns
$t_{rB}$	Output Rise Time			Open-Drain	145			106			58			ns
$t_{fA}$	Output Fall Time	B	A	Push-Pull	5			5			5			ns
$t_{fA}$	Output Fall Time			Open-Drain	6			6			6			ns
$t_{fB}$	Output Fall Time	A	B	Push-Pull	7			7			8			ns
$t_{fB}$	Output Fall Time			Open-Drain	13			16			16			ns

### 5.7 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2V$

over operating free-air temperature range (unless otherwise noted)

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage ( $V_{CCB}$ )						UNIT			
					2.5 ± 0.2V			3.3 ± 0.3V				5.0 ± 0.5V		
					MIN	TYP	MAX	MIN	TYP	MAX		MIN	TYP	MAX
$t_{PHL}$	Propagation Delay (High-to-Low)	A	B	Push-Pull	3			3.4			5			ns
$t_{PHL}$	Propagation Delay (High-to-Low)			Open-Drain	6.3			6			5.8			ns
$t_{PHL}$	Propagation Delay (High-to-Low)			Push-Pull	3			4			4			ns
$t_{PHL}$	Propagation Delay (High-to-Low)			Open-Drain	200			160			120			ns
$t_{PHL}$	Propagation Delay (High-to-Low)	B	A	Push-Pull	3			3			4			ns
$t_{PHL}$	Propagation Delay (High-to-Low)			Open-Drain	4.7			4.2			4			ns
$t_{PHL}$	Propagation Delay (High-to-Low)			Push-Pull	2.1			2			1.9			ns
$t_{PHL}$	Propagation Delay (High-to-Low)			Open-Drain	173			120			90			ns
$t_{en}$	Enable Time	OE	A or B	-40°C to 85°C	200			200			200			ns

## 5.7 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2V$ (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage ( $V_{CCB}$ )						UNIT			
					$2.5 \pm 0.2V$			$3.3 \pm 0.3V$				$5.0 \pm 0.5V$		
					MIN	TYP	MAX	MIN	TYP	MAX		MIN	TYP	MAX
$t_{dis}$	Disable Time	OE	A or B	-40°C to 85°C	250			250			250			ns
$t_{rA}$	Output Rise Time	B	A	Push-Pull	7			6			5			ns
$t_{rA}$	Output Rise Time			Open-Drain	149			101			63			ns
$t_{rB}$	Output Rise Time	A	B	Push-Pull	8			7			6			ns
$t_{rB}$	Output Rise Time			Open-Drain	150			101			63			ns
$t_{fA}$	Output Fall Time	B	A	Push-Pull	5.1			5.2			5			ns
$t_{fA}$	Output Fall Time			Open-Drain	6			6			5			ns
$t_{fB}$	Output Fall Time	A	B	Push-Pull	7			6.4			8.7			ns
$t_{fB}$	Output Fall Time			Open-Drain	8			9			10			ns

## 5.8 Switching Characteristics, $V_{CCA} = 3.3 \pm 0.3V$

over operating free-air temperature range (unless otherwise noted)

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage ( $V_{CCB}$ )						UNIT
					$3.3 \pm 0.3V$			$5.0 \pm 0.5V$			
					MIN	TYP	MAX	MIN	TYP	MAX	
$t_{PHL}$	Propagation Delay (Hight-to-Low)	A	B	Push-Pull	2.4			3.1			ns
$t_{PHL}$	Propagation Delay (Hight-to-Low)			Open-Drain	4.2			4.6			
$t_{PLH}$	Propagation Delay (Low-to-High)			Push-Pull	4.2			4.4			
$t_{PLH}$	Propagation Delay (Low-to-High)			Open-Drain	160			120			
$t_{PHL}$	Propagation Delay (Hight-to-Low)	B	A	Push-Pull	2.5			3.3			ns
$t_{PHL}$	Propagation Delay (Hight-to-Low)			Open-Drain	4.5			4			ns
$t_{PLH}$	Propagation Delay (Low-to-High)			Push-Pull	2.5			2.6			ns
$t_{PLH}$	Propagation Delay (Low-to-High)			Open-Drain	139			105			ns
$t_{en}$	Enable Time	OE	A or B	-40°C to 85°C	200			200			ns
$t_{dis}$	Disable Time	OE	A or B	-40°C to 85°C	250			250			ns
$t_{rA}$	Output Rise Time	B	A	Push-Pull	5			4			ns
$t_{rA}$	Output Rise Time			Open-Drain	116			85			ns
$t_{rB}$	Output Rise Time	A	B	Push-Pull	6			7			ns
$t_{rB}$	Output Rise Time			Open-Drain	116			116			ns
$t_{fA}$	Output Fall Time	B	A	Push-Pull	8			7.6			ns
$t_{fA}$	Output Fall Time			Open-Drain	6			5			ns
$t_{fB}$	Output Fall Time	A	B	Push-Pull	8.2			10.8			ns
$t_{fB}$	Output Fall Time			Open-Drain	7			8			ns

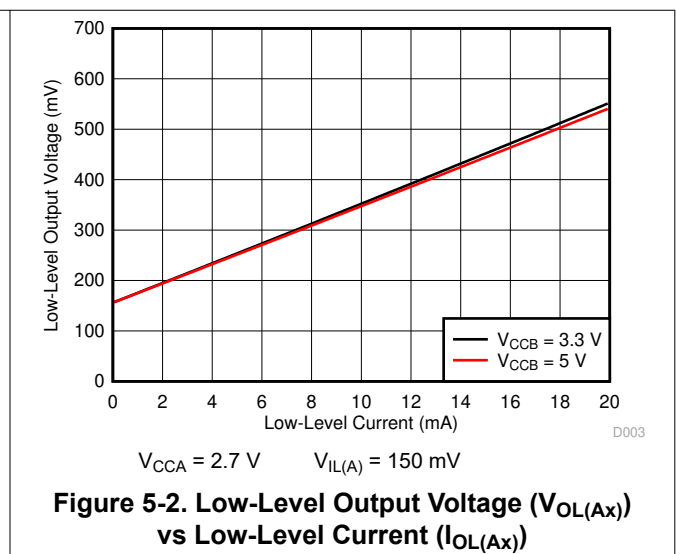
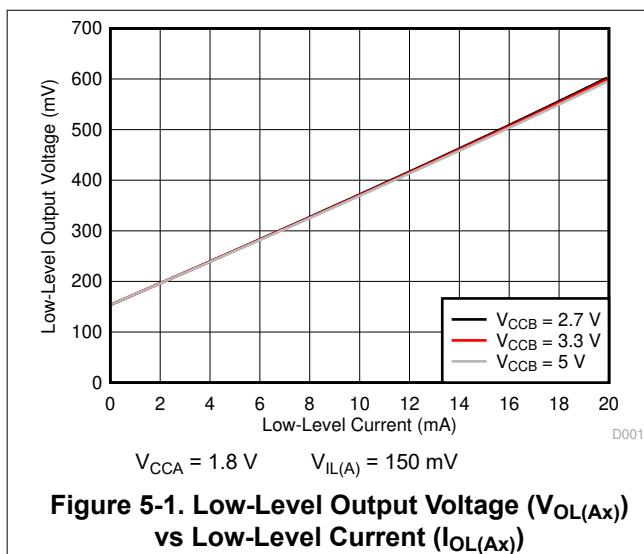


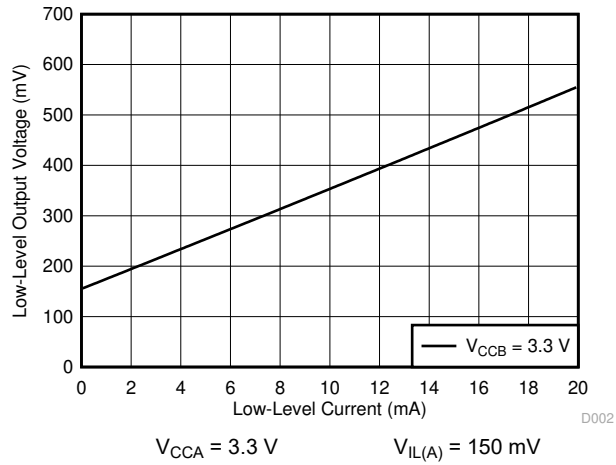
### 5.9 Switching Characteristics: $T_{sk}$ , $T_{MAX}$

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	$V_{CCA}$	$V_{CCB}$	Operating free-air temperature ( $T_A$ )			UNIT
				-40°C to 85°C			
				MIN	TYP	MAX	
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Push-Pull Driving	1.8 ± 0.15V	2.5V ± 0.2V		18	Mbps
			1.8 ± 0.15V	3.3V ± 0.3V		21	
			1.8 ± 0.15V	5V ± 0.5V		23	
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Push-Pull Driving	2.5V ± 0.2V	2.5V ± 0.2V		20	Mbps
			2.5V ± 0.2V	3.3V ± 0.3V		22	
			2.5V ± 0.2V	5V ± 0.5V		24	
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Push-Pull Driving	3.3V ± 0.3V	3.3V ± 0.3V		22	Mbps
			3.3V ± 0.3V	5V ± 0.5V		24	
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Open-Drain Driving	1.8 ± 0.15V	2.5V ± 0.2V		2	Mbps
			1.8 ± 0.15V	3.3V ± 0.3V		2	
			1.8 ± 0.15V	5V ± 0.5V		2	
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Open-Drain Driving	2.5V ± 0.2V	2.5V ± 0.2V		2	Mbps
			2.5V ± 0.2V	3.3V ± 0.3V		2	
			2.5V ± 0.2V	5V ± 0.5V		2	
TMAX - Maximum Data Rate	50% Duty Cycle Input One channel switching	Open-Drain Driving	3.3V ± 0.3V	3.3V ± 0.3V		2	Mbps
			3.3V ± 0.3V	5V ± 0.5V		2	
$t_w$	Pulse Duration, Data Inputs	Push-Pull Driving	1.65V to 3.3V	2.3V to 5.5V	41		ns
			Open-Drain Driving	1.65V to 3.3V	2.3V to 5.5V	500	
$t_{sk}$ - Output skew	Skew between any two outputs of the same package switching in the same direction	Push-Pull Driving	1.65V to 3.3V	2.3V to 5.5V		1	ns
			Open-Drain Driving	1.65V to 3.3V	2.3V to 5.5V		

### 5.10 Typical Characteristics

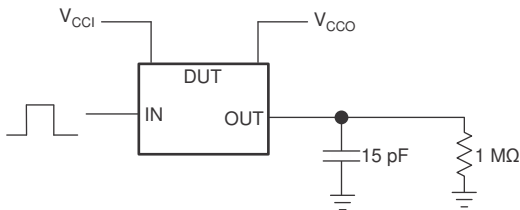




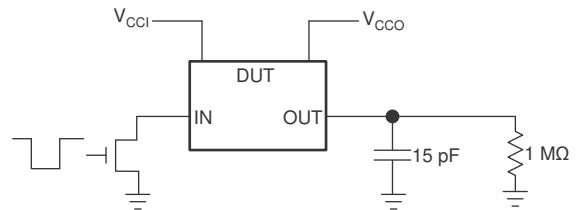
**Figure 5-3. Low-Level Output Voltage ( $V_{OL(Ax)}$ ) vs Low-Level Current ( $I_{OL(Ax)}$ )**

## 6 Parameter Measurement Information

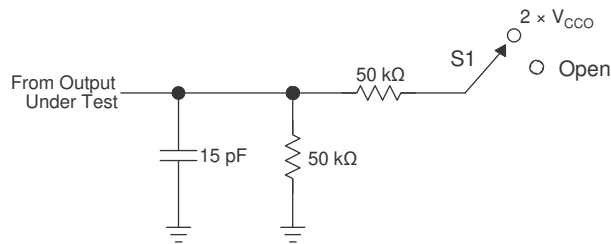
### 6.1 Load Circuits



**Figure 6-1. Data Rate, Pulse Duration, Propagation Delay, Output Rise-Time and Fall-Time Measurement Using a Push-Pull Driver**



**Figure 6-2. Data Rate, Pulse Duration, Propagation Delay, Output Rise-Time and Fall-Time Measurement Using an Open-Drain Driver**



TEST	S1
$t_{PZL} / t_{PLZ}$ ( $t_{dis}$ )	$2 \times V_{CCO}$
$t_{PHZ} / t_{PZH}$ ( $t_{en}$ )	Open

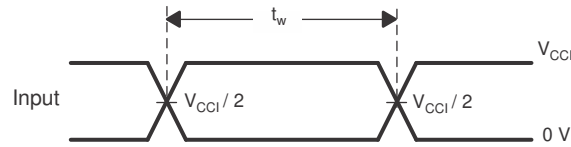
**Figure 6-3. Load Circuit for Enable-Time and Disable-Time Measurement**

1.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
2.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
3.  $V_{CCI}$  is the  $V_{CC}$  associated with the input port.
4.  $V_{CCO}$  is the  $V_{CC}$  associated with the output port.

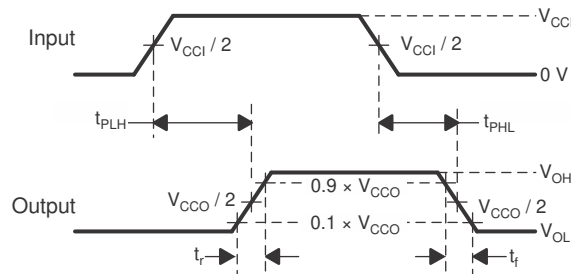
## 6.2 Voltage Waveforms

The outputs are measured one at a time, with one transition per measurement. All input pulses are supplied by generators that have the following characteristics:

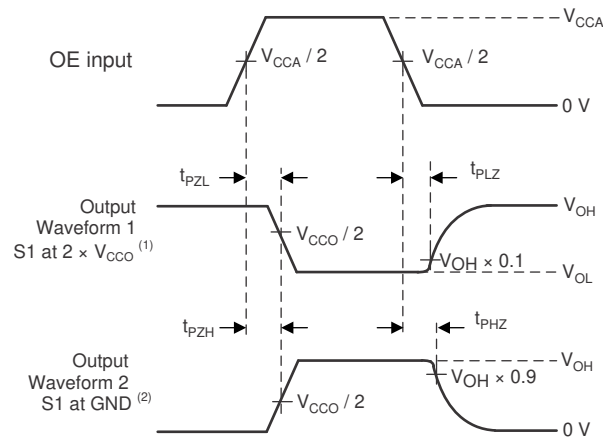
- $PRR \leq 10\text{MHz}$
- $Z_O = 50\Omega$
- $dv/dt \geq 1\text{V/ns}$



**Figure 6-4. Pulse Duration**



**Figure 6-5. Propagation Delay Times**



- A. Waveform 1 is for an output with internal such that the output is high, except when OE is high (see [Figure 6-3](#)).
- B. Waveform 2 is for an output with conditions such that the output is low, except when OE is high.

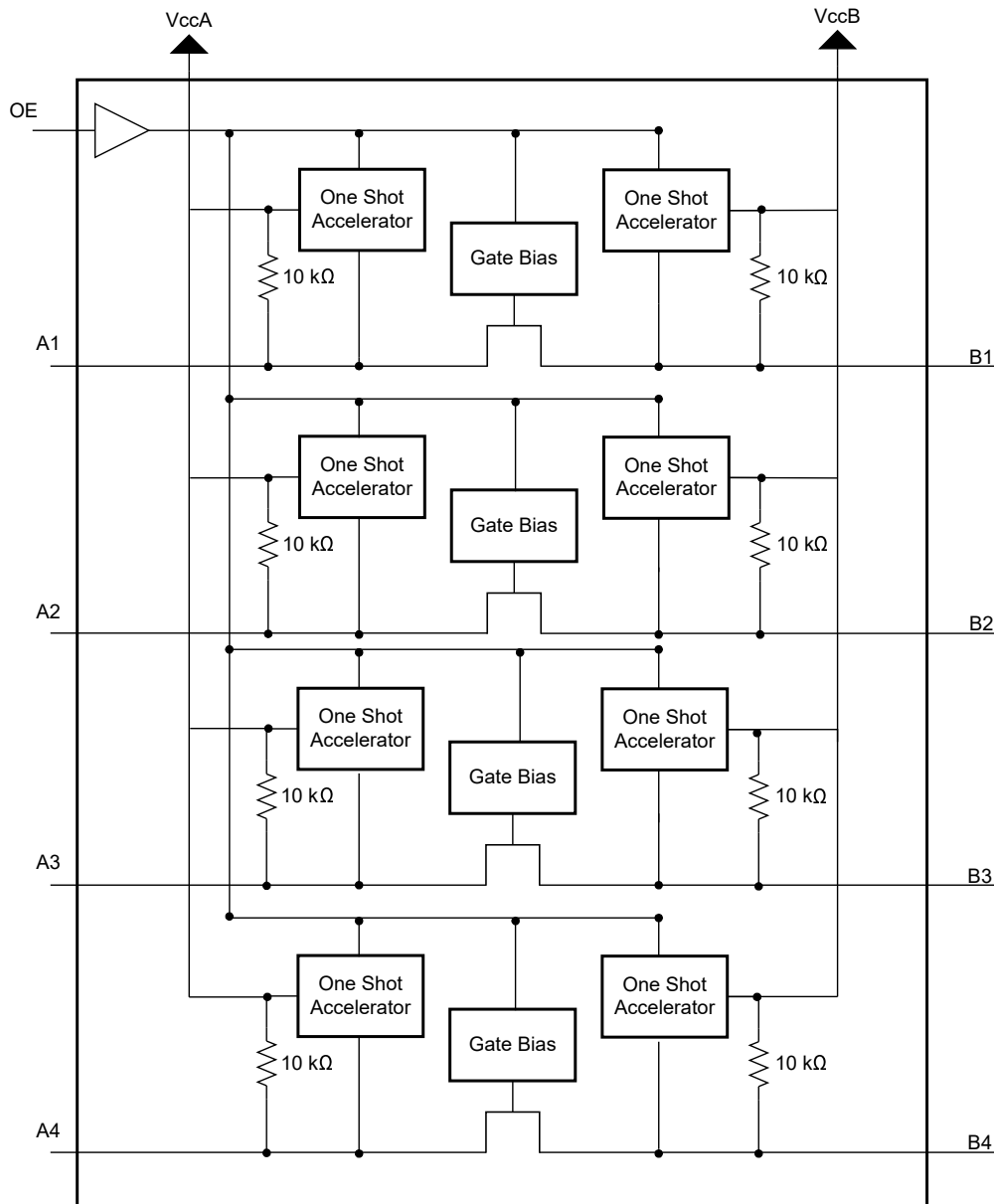
**Figure 6-6. Enable and Disable Times**

## 7 Detailed Description

### 7.1 Overview

The TXS0104V device is a directionless voltage-level translator specifically designed for translating logic voltage levels. The A port is able to accept I/O voltages ranging from 1.65V to 3.6V, while the B port can accept I/O voltages from 2.3V to 5.5V. The device is a pass gate architecture with edge rate accelerators (one shots) to improve the overall data rate. 10kΩ pullup resistors, commonly used in open drain applications, have been conveniently integrated so that an external resistor is not needed. While this device is designed for open drain applications, the device can also translate push-pull CMOS logic outputs.

### 7.2 Functional Block Diagram



## 7.3 Feature Description

### 7.3.1 Architecture

The TXS0104V architecture (see Figure 7-1) does not require a direction-control signal to control the direction of data flow from A to B or from B to A.

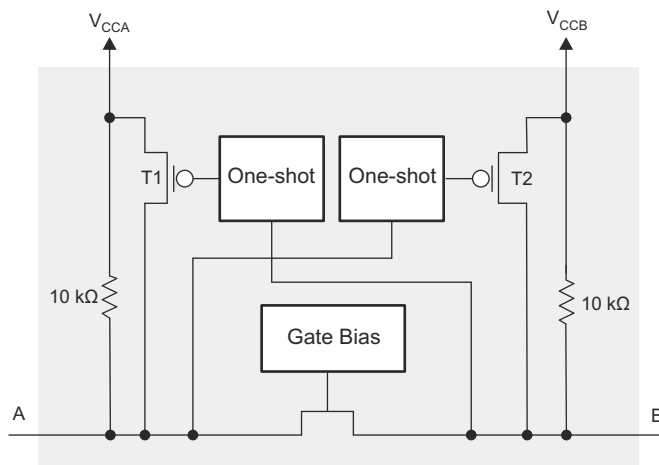


Figure 7-1. Architecture of a TXS0104V Cell

Each A-port I/O has an internal 10kΩ pullup resistor to  $V_{CCA}$ , and each B-port I/O has an internal 10kΩ pullup resistor to  $V_{CCB}$ . The output one-shots detect rising edges on the A or B ports. During a rising edge, the one-shot turns on the PMOS transistors (T1 and T2) for a short duration which speeds up the low-to-high transition.

### 7.3.2 Input Driver Requirements

The fall time ( $t_{fA}$  and  $t_{fB}$ ) of a signal depends on the output impedance of the external device driving the data I/Os of the TXS0104V device. Similarly, the  $t_{pHL}$  and maximum data rates also depend on the output impedance of the external driver. The values for  $t_{fA}$ ,  $t_{fB}$ ,  $t_{pHL}$ , and maximum data rates in the data sheet assume that the output impedance of the external driver is less than 50Ω.

### 7.3.3 Power Up

During operation, ensure that  $V_{CCA} \leq V_{CCB}$  at all times. During power-up sequencing,  $V_{CCA} \geq V_{CCB}$  does not damage the device, so any power supply can be ramped up first.

### 7.3.4 Enable and Disable

The TXS0104V device has an OE input that disables the device by setting OE low, which places all I/Os in the high-impedance state. The disable time ( $t_{dis}$ ) indicates the delay between the time when the OE pin goes low and when the outputs actually enter the high-impedance state. The enable time ( $t_{en}$ ) indicates the amount of time the user must allow for the one-shot circuitry to become operational after the OE pin is taken high.

### 7.3.5 Pullup and Pulldown Resistors on I/O Lines

Each A-port I/O has an internal 10kΩ pullup resistor to  $V_{CCA}$ , and each B-port I/O has an internal 10kΩ pullup resistor to  $V_{CCB}$ . If a smaller value of pullup resistor is required, an external resistor must be added from the I/O to  $V_{CCA}$  or  $V_{CCB}$  (in parallel with the internal 10kΩ resistors).

## 7.4 Device Functional Modes

The TXS0104V device has two functional modes: enabled and disabled. To disable the device set the OE input low, which places all I/Os in a high impedance state. Setting the OE input high will enable the device.

## 8 Application and Implementation

### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 8.1 Application Information

The TXS0104V device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The TXS0104V device is an excellent choice for applications where an open-drain driver is connected to the data I/Os. The TXS0104V device can also be used in applications where a push-pull driver is connected to the data I/Os, but the TXB0104 device might be a better option for such push-pull applications.

### 8.2 Typical Application

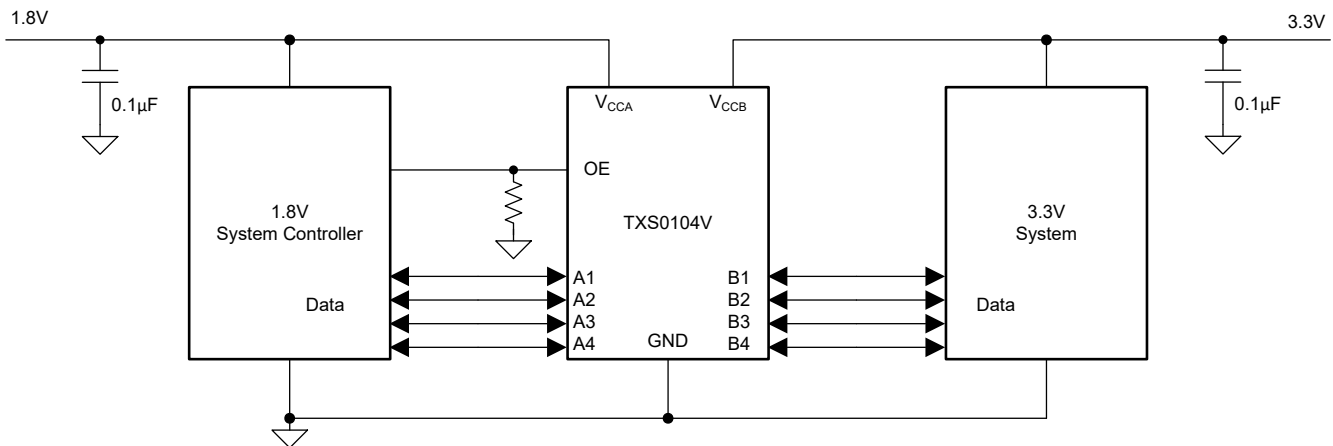


Figure 8-1. Application Schematic

#### 8.2.1 Design Requirements

For this design example, use the parameters listed in [Table 8-1](#).

Table 8-1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
Input voltage range	1.65 to 3.6V
Output voltage range	2.3 to 5.5V

### 8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

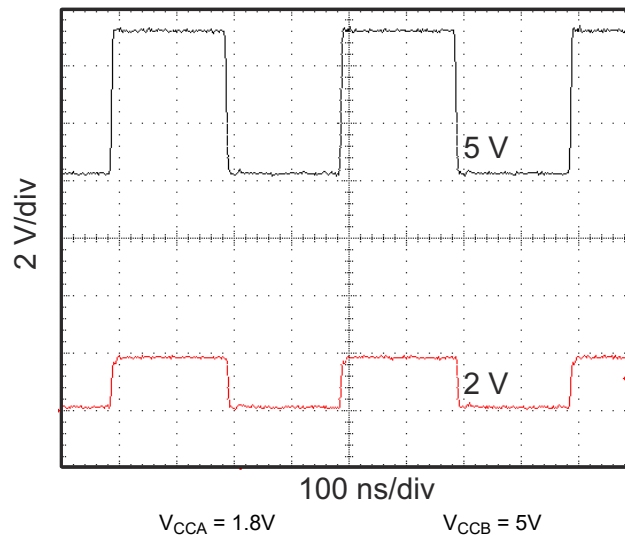
- Input voltage range
  - Use the supply voltage of the device that is driving the TXS0104V device to determine the input voltage range. For a valid logic high the value must exceed the  $V_{IH}$  of the input port. For a valid logic low the value must be less than the  $V_{IL}$  of the input port.
- Output voltage range
  - Use the supply voltage of the device that the TXS0104V device is driving to determine the output voltage range.
  - The TXS0104V device has 10k $\Omega$  internal pullup resistors. External pullup resistors can be added to reduce the total RC of a signal trace if necessary.
- An external pull down resistor decreases the output  $V_{OH}$  and  $V_{OL}$ . Use [Equation 1](#) to calculate the  $V_{OH}$  as a result of an external pull down resistor.

$$V_{OH} = V_{CCx} \times R_{PD} / (R_{PD} + 10 \text{ k}\Omega) \quad (1)$$

where

$V_{CCx}$  is the supply voltage on either  $V_{CCA}$  or  $V_{CCB}$   
 $R_{PD}$  is the value of the external pull down resistor

### 8.2.3 Application Curve



**Figure 8-2. Level-Translation of a 2.5MHz Signal**



### 8.3 Power Supply Recommendations

The TXS0104V device uses two separate configurable power-supply rails,  $V_{CCA}$  and  $V_{CCB}$ .  $V_{CCB}$  accepts any supply voltage from 2.3V to 5.5V and  $V_{CCA}$  accepts any supply voltage from 1.65V to 3.6V as long as  $V_S$  is less than or equal to  $V_{CCB}$ . The A port and B port are designed to track  $V_{CCA}$  and  $V_{CCB}$  respectively allowing for low-voltage bidirectional translation between any of the 1.8V, 2.5V, 3.3V, and 5V voltage nodes.

The TXS0104V device does not require power sequencing between  $V_{CCA}$  and  $V_{CCB}$  during power-up so the power-supply rails can be ramped in any order. A  $V_{CCA}$  value greater than or equal to  $V_{CCB}$  ( $V_{CCA} \geq V_{CCB}$ ) does not damage the device, but during operation,  $V_{CCA}$  must be less than or equal to  $V_{CCB}$  ( $V_{CCA} \leq V_{CCB}$ ) at all times.

The output-enable (OE) input circuit is designed so that it is supplied by  $V_{CCA}$  and when the (OE) input is low, all outputs are placed in the high-impedance state. For the high-impedance state of the outputs during power up or power down, the OE input pin must be tied to GND through a pulldown resistor and must not be enabled until  $V_{CCA}$  and  $V_{CCB}$  are fully ramped and stable. The current-sourcing capability of the driver determines the minimum value of the pulldown resistor to ground.

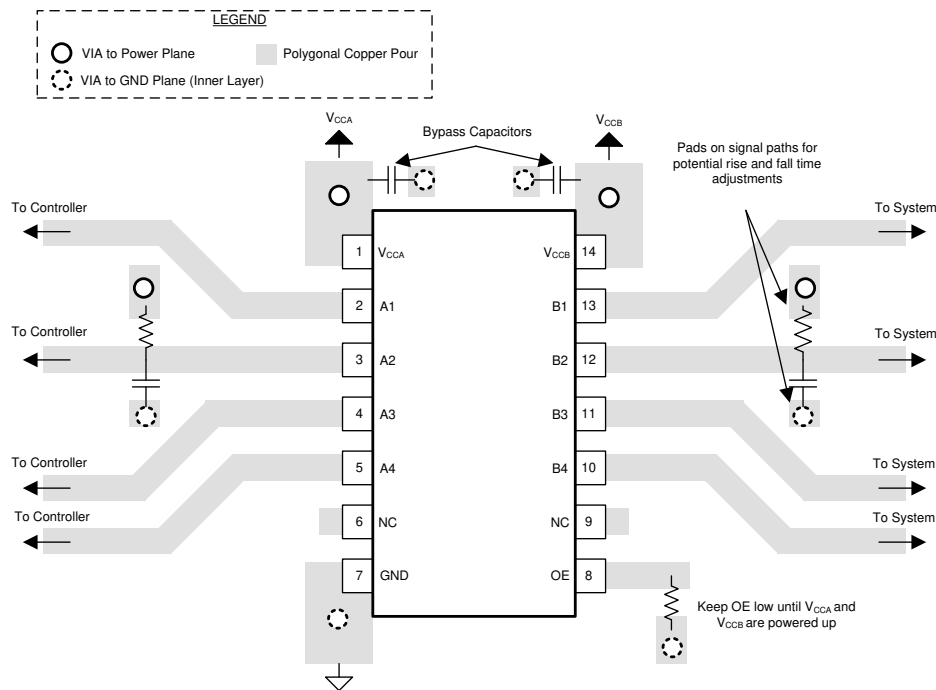
### 8.4 Layout

#### 8.4.1 Layout Guidelines

For device reliability, it is recommended to follow common printed-circuit board layout guidelines such as follows:

- Bypass capacitors should be used on power supplies.
- Short trace lengths should be used to avoid excessive loading.
- PCB signal trace-lengths must be kept short enough so that the round-trip delay of any reflection is less than the one shot duration, approximately 30ns, and encounters low impedance at the source driver.
- Placing pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depending on the system requirements

#### 8.4.2 Layout Example



**Figure 8-3. TXS0104V Layout Example**

## 9 Device and Documentation Support

### 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [Effects of External Pullup and Pulldown Resistors on TXS and TXB Devices application report](#)
- Texas Instruments, [Basics of Voltage Translation application report](#)
- Texas Instruments, [A Guide to Voltage Translation With TXS-Type Translators application report](#)

### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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### 9.4 Trademarks

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### 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 10 Revision History

DATE	REVISION	NOTES
June 2024	*	Initial Release

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TXS0104VBQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YF04V	<a href="#">Samples</a>
TXS0104VDR	ACTIVE	SOIC	D	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TXS0104V	<a href="#">Samples</a>
TXS0104VQBQARQ1	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YF04VQ	<a href="#">Samples</a>
TXS0104VQRUTRQ1	ACTIVE	UQFN	RUT	12	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	1SW	<a href="#">Samples</a>
TXS0104VRGYR	ACTIVE	VQFN	RGY	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YF04V	<a href="#">Samples</a>
TXS0104VRUTR	ACTIVE	UQFN	RUT	12	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	1SV	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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